

Continental Device India Limited



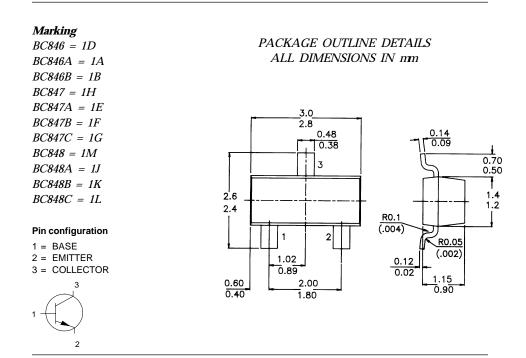


SOT-23 Formed SMD Package

BC846 BC847 BC848

SILICON PLANAR EPITAXIAL TRANSISTORS

General purpose N-P-N transistors



ABSOLUTE MAXIMUM RATINGS

			BC846	BC847	BC848
Collector-emitter voltage ($V_{BE} = 0$)	$V_{C\!E\!S}$	max.	80	50	30 V
Collector-emitter voltage (open base)	V_{CE0}	max.	65	45	30 V
Collector current (peak value)	I_{CM}	max.	200	200	200 mA
Total power dissipation up					
to $T_{amb} = 25$ °C	P_{tot}	max.	<i>250</i>	250	<i>250</i> mW
Junction temperature	T_{j}	max.	<i>150</i>	150	150 ° C
Small-signal current gain	•				
$I_C = 2 \text{ mA}$; $V_{CF} = 5 \text{ V}$; $f = 1 \text{ kHz}$	$h_{f\!e}$	>	125	125	125
IC = 2 IIIA, VCE = 3 V, I = 1 M12	n _{Ie}	<	<i>500</i>	900	900
Transition frequency at $f = 100 \text{ MHz}$					
$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$	f_T	>	100	> 100	$> 100 { m MHz}$
Noise figure at $R_S = 2 \text{ kW}$					
$I_C = 200 \text{ mA}; \ V_{CE} = 5 \ V$					
f = 1 kHz; B = 200 Hz	F	typ.	2	2	2 dB

RATINGS (at	$T_A = 25^{\circ}C$	unless	otherwise	specified)
Limiting value	es			

Liming values			BC846	BC84	7 BC84	R
Collector-base voltage (open emitter)	V_{CBO}	max.	80	50	30	-
Collector–emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	80	50	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	65	45	30	V
Emitter-base voltage (open collector)	V_{EBO}	max.		6	5	V
Collector current (d.c.)	I_C	max.		100		mΑ
Collector current (peak value)	I_{CM}	max.		200		mΑ
Emitter current (peak value)	$-I_{EM}$	max.		200		mΑ
Base current (peak value)	I_{BM}	max.		200		mΑ
Total power dissipation*	Divi					
up to T _{amb} : 25 °C	P_{tot}	max.		250		mW
Storage temperature	T_{stg}		-55	to +	<i>150</i>	$^{\circ}$ C
Junction temperature	T_j	max.		150		$^{\circ}$ C
THERMAL RESISTANCE						
From junction to ambient			F	th j-a	= 500	KW
CHARACTERISTICS						
$T_i = 25$ °C unless otherwise specified						
Collector cut-off current						
$I_E = 0; \ V_{CB} = 30 \ V$			I_{CBO}	<	15	nΑ
$I_E = 0$; $V_{CB} = 30 \text{ V}$; $T_i = 150 \text{ °C}$			I_{CBO}	<	5	$\mathfrak{m}A$
Base-emitter voltage			СВО			
$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$			V_{BE}	typ.	660	mV
			580 to	700		mV
$I_C = 10 \text{ mA; } V_{CE} = 5 \text{ V}$			V_{BE}	<	770	mV
Saturation voltage						
$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$			V _{CEsat}	tvp.	90	mV
C			CLSat	<		mV
			V _{BEsat}	typ.		mV
$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$			V _{CEsat}	tvn	200	mV
$I_C = 100 \text{ Hz}$ i, $I_B = 0 \text{ Hz}$ i			V CESal	<i>typ.</i> <		mV
			Vpr.			mV
Collector capacitance at $f = 1$ MHz			V _{BEsat}	typ.	900	IIIV
$I_E = I_e = 0$; $V_{CB} = 10 \text{ V}$			C_{c}	typ.	2,5	рF
Transition frequency at $f = 100$ MHz			- (JF.	,-	F-
$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$			f_T	>	100	MHz
Noise figure at $R_S = 2 \text{ KW}$						
$I_C = 200 \text{ mA}; V_{CE} = 5 \text{ V};$						
f = 1 kHz; B = 200 Hz				typ.	2	dВ
•			F	<		dВ
					-	

					BC846A	BC846B	
				BC847	BC847A	BC847B	BC847C
			BC846	BC848	BC848A	BC848B	BC848C
DC current gain $I_C = 10 \text{ mA}; V_{CE} = 5V$	hFE	typ.			90	150	270
$I_C = 2 \text{ mA}; \ V_{CE} = 5 \text{ V}$	h_{FE}	>	110	110	110	200	420
		typ.			180	290	520
		<	450	800	220	450	800
Small signal current gain at $f = 1 \text{ kHz}$	h_{fe}					l	ı
$I_C = 2 \text{ mA}; V_{CE} = 5V$		>	125	125			
		<	<i>500</i>	900			

Disclaimer

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